

DOCKET NO: 249248US2DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
MASAYOSHI HIRAO, ET AL. : ATTN: APPLICATION DIVISION  
SERIAL NO: NEW APPLICATION :  
FILED: HEREWITH :  
FOR: SEMICONDUCTOR DEVICE WITH :  
SEMICONDUCTOR CHIP FORMED BY :  
USING WIDE GAP SEMICONDUCTOR :  
AS BASE MATERIAL

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 3 of this paper.

**Remarks** begin on page 8 of this paper.